

ABSTRACT**A DEVICE AND A METHOD FOR FORMING A FERROELECTRIC
CAPACITOR DEVICE**

A ferroelectric capacitor device, such as an FeRAM device is formed by forming a substrate extending in a first plane and comprising a number of layers of material, forming a hard mask layer on the substrate and forming a first layer of a first material on the hard mask layer. The hard mask shape is then defined by etching the hard mask layer. A second layer of the first material is deposited on the etched hard mask layer. The deposited second layer has one or more side surfaces extending substantially perpendicular to the plane of the substrate. The second layer and the number of layers forming the substrate are then etched to shape the ferroelectric capacitor device.